



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Li et al.	)	
Serial No.:	09/662,682	the United States in an envelope a	hat this paper is being deposited with s Postal Service as FIRST-CLASS mail ddressed to: Assistant Commissioner hington, D.C. 20231, on this date.
Filed:	September 15, 2000	Oct, 2,2002	ais BR
For:	METAL-ASSISTED CHEMICAL ETCH POROUS SILICON FORMATION METHOD	Date F-CLASS.WCM Appr. February 20, 1998	Registration No. <u>43,874</u> Attorney for Applicant
Art Unit:	1765	) ) ) .	RECEIVED
Examiner:	Vinh, Lan	)	OCT 0 9 2002
	RESPONSE B		TC 1700

Assistant Commissioner for Patents Washington, D.C. 20231

Dear Sir:

In response to the Office Action mailed August 2, 2002, which has been made final, please consider the following Remarks.

## **REMARKS**

Claims 1-7, 9, 10-17, 19, and 20 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Russell in view of Yoshikawa. Claims 8 and 18 stand rejected under 35 U.S.C. §103(a) as being unpatentable over Russell in view of Yoshikawa, and further in view of Yamagata. Claim 21 stands rejected under 35 U.S.C. §103(a) as being unpatentable over Russell in view of Yoshikawa. Applicants respectfully traverse the rejection.